
HSB226S

Silicon Schottky Barrier Diode

HITACHI

ADE-208-961(Z)

Rev. 0
Jul. 2000

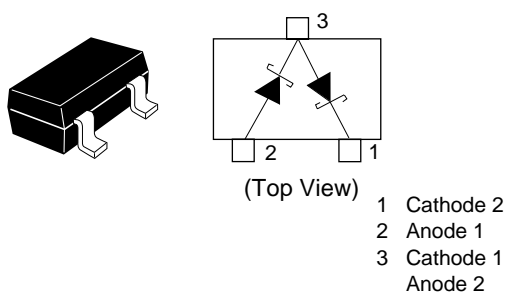
Features

- Low reverse current, Low capacitance.
- CMPAK Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HSB226S | E7 | CMPAK |

Outline



HSB226S

Absolute Maximum Ratings

(Ta = 25°C)

| Item | Symbol | Value | Unit |
|---|------------------|-------------|------|
| Repetitive peak reverse voltage | V_{RRM} | 25 | V |
| Non-Repetitive peak forward surge current | I_{FSM}^{*1*2} | 200 | mA |
| forward current | I_F^{*2} | 50 | mA |
| Junction temperature | Tj | 125 | °C |
| Storage temperature | Tstg | -55 to +125 | °C |

Notes: 1. 10msec sine wave 1 pulse
2. Two device total

Electrical Characteristics

(Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
|-----------------|----------|-----|-----|------|------|--|
| Forward voltage | V_{F1} | — | — | 0.33 | V | $I_F = 1 \text{ mA}$ |
| | V_{F2} | — | — | 0.38 | V | $I_F = 5 \text{ mA}$ |
| Reverse current | I_R | — | — | 0.45 | μA | $V_R = 20 \text{ V}$ |
| Capacitance | C | — | — | 2.80 | pF | $V_R = 1 \text{ V}, f = 1 \text{ MHz}$ |

Note: Per one device

Main Characteristic

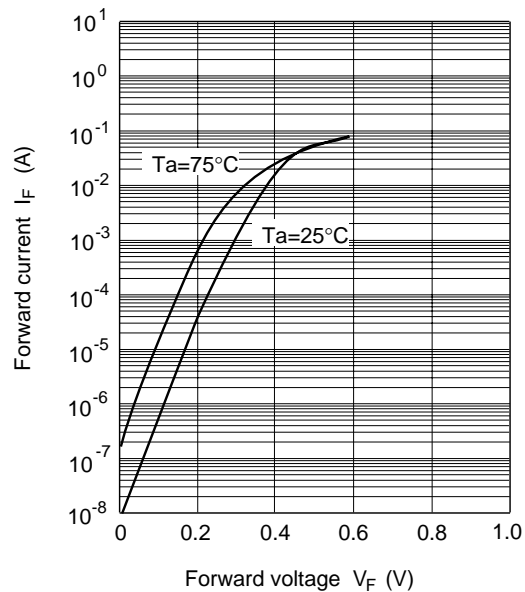


Fig.1 Forward current Vs. Forward voltage

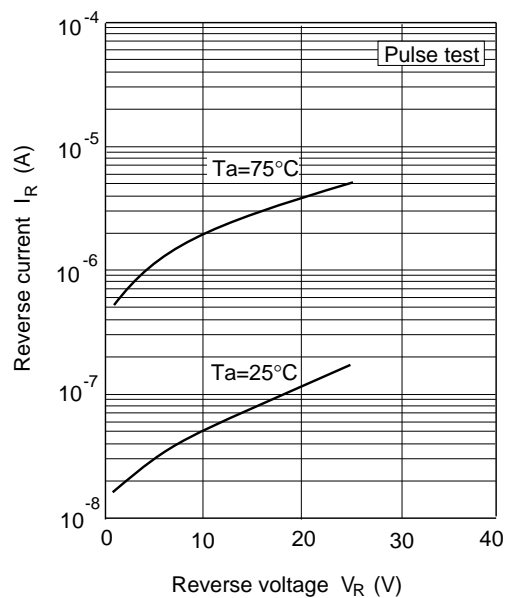


Fig.2 Reverse current Vs. Reverse voltage

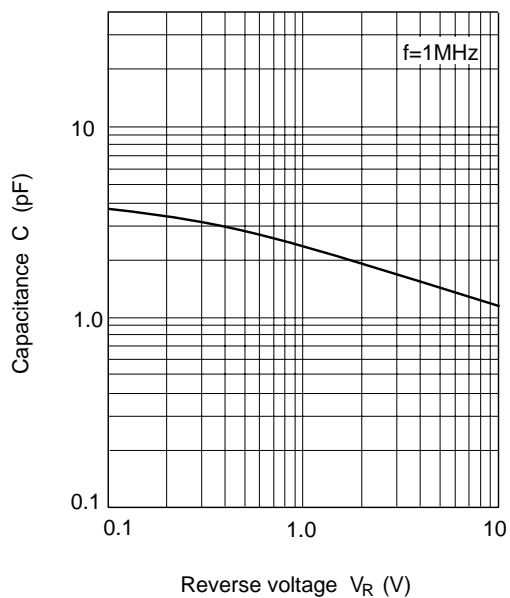
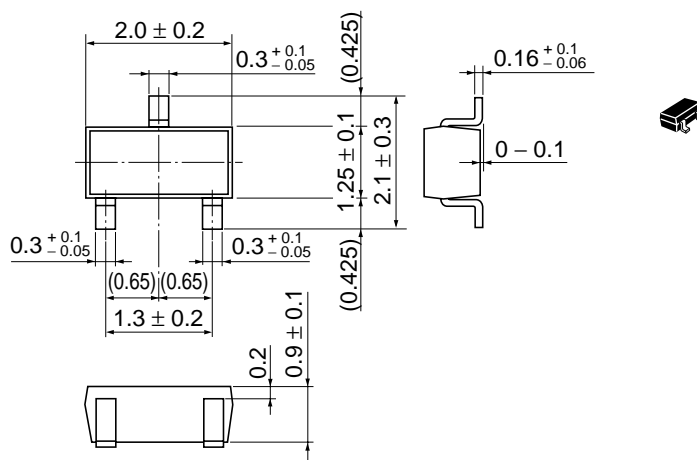


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



| | |
|------------------------|----------|
| Hitachi Code | CMPAK |
| JEDEC | — |
| EIAJ | Conforms |
| Mass (reference value) | 0.006 g |

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